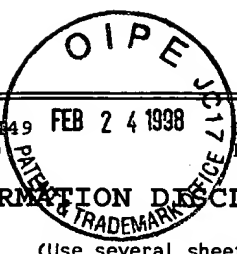


attach #20



Form PTO-1449 FEB 24 1998 U.S. Department of Commerce
(Rev. 8-83) Patent and Trademark Office

Attorney Docket N. 0756-1614	Serial N. 08/781,920
Applicant: Takashi FUKUNAGA et al	
Filing Date: Dec 30, 1996	Group: 1442-1762

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,426,064	06/20/95	Zhang et al			
	5,481,121	01/02/96	Zhang et al			
	5,488,000	01/30/96	Zhang et al			
	5,508,533	04/16/96	Takemura			
	5,534,716	07/09/96	Takemura			
	5,563,426	10/08/96	Zhang et al			
	5,569,936	10/29/96	Zhang et al			
	5,580,792	12/03/96	Zhang et al			
	5,589,694	12/31/96	Takayama et al			
	5,595,923	01/21/97	Zhang et al			
	5,595,944	01/21/97	Zhang et al			

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner	Date Considered 5/10/98
----------	-------------------------

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)

FEB 24 1998

U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket N. 0756-1614

Serial No. 08/781,920

INFORMATION DISCLOSURE STATEMENT

(Use separate sheets if necessary)

Applicant: Takeshi FUKUNAGA et al

Filing Date: Dec 30, 1996

Group: 1112

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,604,360	02/18/97	Zhang et al			
	5,605,846	02/25/97	Ohtani et al			
	5,606,179	02/25/97	Yamazaki et al			
	5,608,232	03/04/97	Yamazaki et al			
	5,612,250	03/18/97	Ohtani et al			
	5,614,426	03/25/97	Funada et al			
	5,614,733	03/25/97	Zhang et al			
	5,616,506	04/01/97	Takemura			
	5,620,910	04/15/97	Teramoto			
	5,621,224	04/15/97	Yamazaki et al			
	5,637,515	06/10/97	Takemura			
	5,643,826	07/01/97	Ohtani et al			
	5,646,424	07/08/97	Zhang et al			
	5,654,203	08/05/97	Ohtani et al			
	5,656,825	08/12/97	Kusumoto et al			
	5,700,333	12/23/97	Yamazaki et al			

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation Yes No	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner

Date Considered

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)

U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket N . 0756-1614

Serial N . 08/781,920

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Takeshi FUKUNAGA et al.

Filing Date: Dec. 30, 1996

Group: 4442-1762

MAR - 9 1998

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
MP	5,597,741	01/28/97	Sakamoto et al.	438	486	
	5,576,222	11/19/96	Arai et al.	438	486	
	5,529,951	06/25/96	Noguchi et al.	438	487	
	5,278,093	01/94	Yonehara	437	173	
	4,659,392	04/87	Vasudev	437	942	
	5,424,230	06/95	Wakai	437	247	
	4,814,292	03/89	Sasaki et al.	437	247	

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation Yes N

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

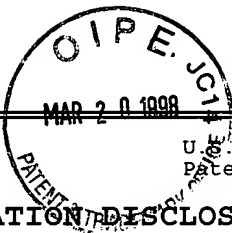
MP	Fuse et al., "Performance of Poly-Si Thin Film Transistors Fabricated by Excimer Laser Annealing of SiH ₄ and Si ₂ H ₆ . Source Low Pressure Vapor Deposited a-Si films with or without Solid-Phase Crystallization", Solid State Phenomena, Vols. 37-38, 1994
	Bonnel et al., "Poly Crystalline Silicon Thin-Film Transistors with Two-Step Annealing Porcess", IEEE, Electron Device Letters, Vol. 14, No. 12, December 1993, pp. 551-553
	Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals", Applied Surface Science, Vol. 36, 1989, pp. 597-604
MP	Nam et al., "Thin Film Transistors with Polycrystalline Silicon Prepared by a new Annealing Method", Jpn. J. Appl. Phys., Vol. 32, 1993, pp. 1908-1912

Examiner r

Date Consider d

5/10/98

*EXAMINER: Initial if citation considered, wh th r or not citation is in conformance with MPEP 609; Draw line through citation if not in conformanc and not consider d. Include c py of this f rm with next c mmunicati n to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket N. 0756-1614

Serial N. 08/781,920

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Takeshi FUKUNAGA et al.

Filing Date: Dec. 30, 1996

Group: 4112-1762

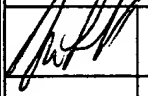
U.S. PATENT DOCUMENTS MAR 27 1998

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Bonnel et al., "Poly Crystalline Silicon Thin-Film Transistors with Two-Step Annealing Process", IEEE, Electron Device Letters, Vol. 14, No. 12, December 1993, pp. 551-553

Examiner

Date Considered

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.